Henning Fouckhardt

List of Publications by Year
in descending order

30 papers	155 citations	1040056 9 h-index	1199594 12 g-index
30 all docs	30 docs citations	30 times ranked	110 citing authors

#	Article	IF	Citations
1	Glass surface modification by lithography-free reactive ion etching in an Ar/CF4-plasma for controlled diffuse optical scattering. Surface and Coatings Technology, 2011, 205, S419-S424.	4.8	18
2	An improved shooting approach for solving the time-independent SchrÃ¶dinger equation for III/V QW structures. Physics Letters, Section A: General, Atomic and Solid State Physics, 2001, 286, 199-204.	2.1	16
3	nm- and Î¼m-Scale Surface Roughness on Glass with Specific Optical Scattering Characteristics on Demand. Advances in OptoElectronics, 2007, 2007, 1-7.	0.6	16
4	GaSb quantum dots on GaAs with high localization energy of 710 meV and an emission wavelength of 1.3 Âµm. Journal of Crystal Growth, 2014, 404, 48-53.	1.5	11
5	Self-pulsation in broad area lasers with transverse-mode selective feedback. Optics Communications, 2006, 265, 642-648.	2.1	10
6	Multitude of glass surface roughness morphologies as a tool box for dosed optical scattering. Applied Optics, 2010, 49, 1364.	2.1	10
7	Dense lying self-organized GaAsSb quantum dots on GaAs for efficient lasers. Beilstein Journal of Nanotechnology, 2011, 2, 333-338.	2.8	10
8	Monitoring of (reactive) ion etching (RIE) with reflectance anisotropy spectroscopy (RAS) equipment. Applied Surface Science, 2015, 328, 120-124.	6.1	10
9	Precise in situ etch depth control of multilayered IIIâ^'V semiconductor samples with reflectance anisotropy spectroscopy (RAS) equipment. Beilstein Journal of Nanotechnology, 2016, 7, 1783-1793.	2.8	9
10	Influence of plasma composition on reflectance anisotropy spectra for in situ IIIâ€"V semiconductor dry-etch monitoring. Applied Surface Science, 2015, 357, 530-538.	6.1	7
11	Doped or Quantum-Dot Layers as In Situ Etch-Stop Indicators for III/V Semiconductor Reactive Ion Etching (RIE) Using Reflectance Anisotropy Spectroscopy (RAS). Micromachines, 2021, 12, 502.	2.9	6
12	In-situ etch-depth control better than 5 nm with reflectance anisotropy spectroscopy (RAS) equipment during reactive ion etching (RIE): A technical RAS application. AIP Advances, 2019, 9, .	1.3	5
13	Generation of Dense Lying Ga(As)Sb Quantum Dots for Efficient Quantum Dot Lasers. Advanced Materials Research, 2013, 684, 285-289.	0.3	4
14	Microfluidic Droplet Array as Optical Irises Actuated via Electrowetting. Advances in OptoElectronics, 2018, 2018, 1-8.	0.6	4
15	Interferometric in-situ III/V semiconductor dry-etch depth-control with Â±0.8â€‰nm best accuracy using a quadruple-Vernier-scale measurement. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2021, 39, 052204.	1.2	4
16	Microdroplet Actuation via Light Line Optoelectrowetting (LL-OEW). International Journal of Analytical Chemistry, 2021, 2021, 1-9.	1.0	4
17	Lithography-Free Technology for the Preparation of Digital Microfluidic (DMF) Lab-Chips with Droplet Actuation by Optoelectrowetting (OEW). International Journal of Analytical Chemistry, 2022, 2022, 1-6.	1.0	4
18	Optoelectrowetting (OEW) with push-actuation of microdroplets at small frequencies and OEW equations revisited. Sensors and Actuators A: Physical, 2022, 334, 113331.	4.1	2

#	Article	IF	Citations
19	X-ray studies and time-resolved photoluminescence on optically pumped antimonide-based midinfrared type-II lasers. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2004, 60, 3387-3392.	3.9	1
20	Atomic layer sensitive in-situ plasma etch depth control with reflectance anisotropy spectroscopy (RAS). , 2017, , .		1
21	Fundamental Transverse Mode Selection (TMS#0) of Broad Area Semiconductor Lasers with Integrated Twice-Retracted 4<i>f</i> Set-Up and Film-Waveguide Lens. Advances in OptoElectronics, 2017, 2017, 1-6.	0.6	1
22	1 ML Wetting Layer upon Ga(As)Sb Quantum Dot (QD) Formation on GaAs Substrate Monitored with Reflectance Anisotropy Spectroscopy (RAS). Advances in OptoElectronics, 2018, 2018, 1-7.	0.6	1
23	1D Confocal Broad Area Semiconductor Lasers (Confocal BALs) for Fundamental Transverse Mode Selection (TMS#0). Advances in OptoElectronics, 2019, 2019, 1-7.	0.6	1
24	Ga(As)Sb/GaAs quantum dots for emission around 1300 nm. , 2013, , .		0
25	Combination of Transverse Mode Selection and Active Longitudinal Mode-Locking of Broad Area Semiconductor Lasers. Advances in OptoElectronics, 2014, 2014, 1-5.	0.6	0
26	Microfluidic Optical Shutter Flexibly <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" id="M1"><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:math>-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" id="M2"><mml:mrow><mml:mi>y</mml:mi></mml:mrow></mml:math> Actuated via Electrowetting-on-Dielectrics with <20â€‰ms Response Time. Advances in Optical Technologies, 2017, 2017, 1-5.	0.8	0
27	Monolithically integrated fourier-optical transverse-mode selector for broad area lasers. , 2017, , .		0
28	Epitaxial Growth of Optoelectronically Active Ga(As)Sb Quantum Dots on Al-Rich AlGaAs with GaAs Capsule Layers. Advances in Materials Science and Engineering, 2021, 2021, 1-10.	1.8	0
29	Theory, simulation, fabrication, and characterization of Galois scattering plates for the optical and the THz spectral range. AIP Advances, 2021, 11, 065130.	1.3	0
30	High shape-accuracy of surface roughnesses upon nano-moulding with optical elastomers. Optical Materials, 2021, 118, 111230.	3.6	0